





100V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -100V
- I_C = -5A High Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -90mV @ -1A
- $R_{SAT} = 60m\Omega$ for a Low equivalent On-Resistance
- h_{FE} Specified up to -10A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)

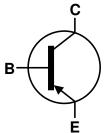
Applications

- Motor Driving
- Line Switching
- High Side Switches
- Subscriber Line Interface Cards (SLIC)

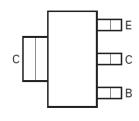




Top View



Device Symbol



Top View Pin-Out

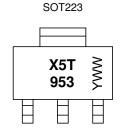
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZX5T953GTA	AEC-Q101	X5T953	7	12	1,000
ZX5T953GQTA	Automotive	X5T953	7	12	1,000

Notes

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



X5T953 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015)



Maximum Ratings (@T_A = +25 ℃, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-5	Α
Peak Pulse Current	I _{CM}	-10	Α

Thermal Characteristics (@TA = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	Б	3.0 24	W
Linear Derating Factor	(Note 7)	P_D	1.6 12.8	mW /℃
Thermal Decistores, Junetics to Ambient	(Note 6)	$R_{ heta JA}$	42	1
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ heta JA}$	78	°C/W
Thermal Resistance Junction to Lead (Note 8)		$R_{ heta JL}$	10.4	
Operating and Storage Temperature Range	T_{J} , T_{STG}	-55 to +150	℃	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.

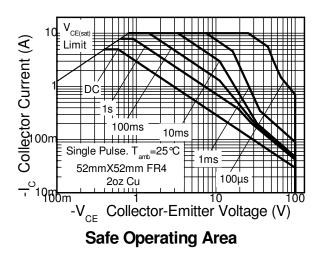
 7. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.

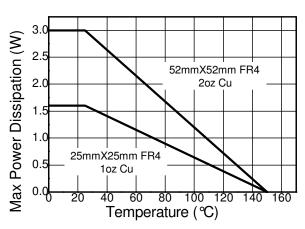
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).

 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

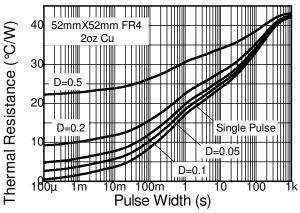


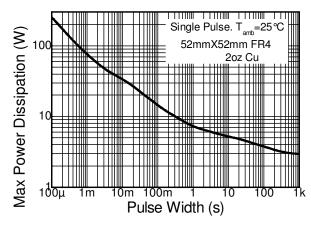
Thermal Characteristics and Derating Information





Derating Curve





Transient Thermal Impedance

Pulse Power Dissipation





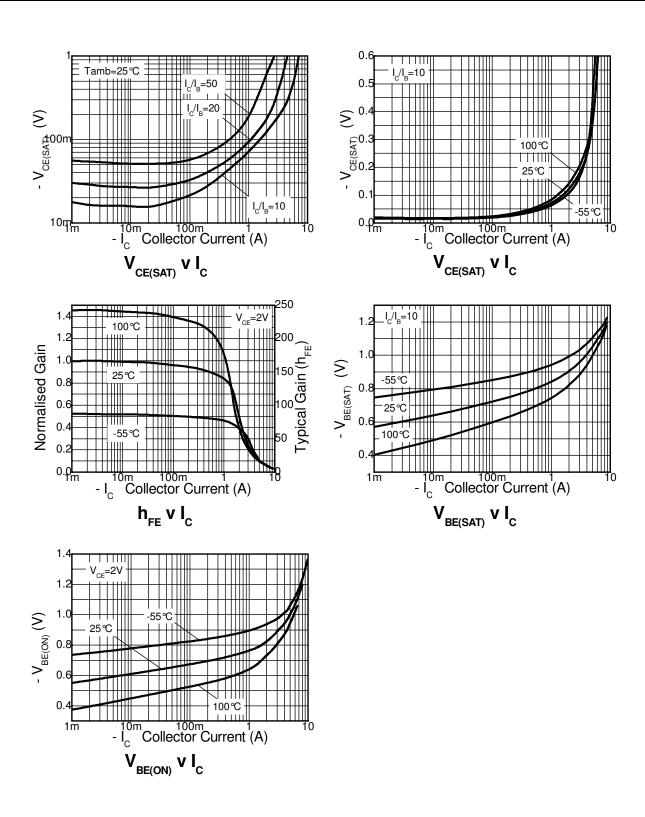
Electrical Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-140	-160	-	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	-140	-160	-	V	$I_C = -1\mu A$, RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-100	-115	-	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	-	V	$I_E = -100 \mu A$
Collector-Base Cut-Off Current	Ісво	-	<1 -	-20 -0.5	n A μA	V _{CB} = -100V V _{CB} = -100V, T _A = +100°C
Collector-Emitter Cut-Off Current	l _{CER} R ≤ 1kΩ	-	<1 -	-20 -0.5	nA μA	V _{CB} = -100V V _{CB} = -100V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	-	<1	-10	nA	$V_{EB} = -6V$
		100	250	-	-	$I_C = -10 \text{mA}, V_{CE} = -1 \text{V}$
		100	200	300		$I_C = -1A$, $V_{CE} = -1V$
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	25	50	-		$I_{C} = -3A, V_{CE} = -1V$
		15	30	-		I _C = -4A, V _{CE} = -1V
		-	5	-		I _C = -10A, V _{CE} = -1V
		-	-20	-30		I _C = -100mA, I _B = -10mA
Collector-Emitter Saturation Voltage (Note 10)	V _{CE(sat)}	-	-70	-90	mV	$I_C = -1A$, $I_B = -100mA$
Collector-Emiller Saturation voltage (Note 10)		-	-120	-150	IIIV	$I_C = -2A$, $I_B = -200mA$
		-	-240	-340		$I_C = -4A$, $I_B = -400mA$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	-985	-1100	mV	$I_C = -4A$, $I_B = -400$ mV
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	-	-920	-1050	mV	$I_{C} = -4A, V_{CE} = -2V$
Output Capacitance (Note 10)	C_obo	-	42	-	pF	V _{CB} = -10V. f = 1MHz
Transition Frequency	f _T	-	125	-	MHz	$V_{CE} = -10V, I_{C} = -100mA$ f = 50MHz
Switching Time	t _{on}	-	42	-	ns	$V_{CC} = -10V, I_{C} = -1A$
Owntoning Time	t _{off}	-	540	-	110	$I_{B1} = I_{B2} = -100 \text{mA}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



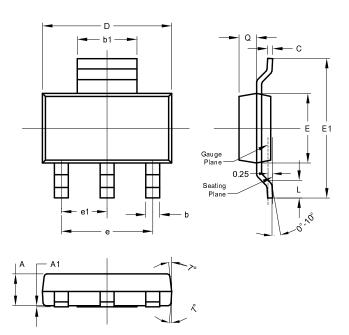
Typical Electrical Characteristics (@TA = +25 ℃, unless otherwise specified.)





Package Outline Dimensions

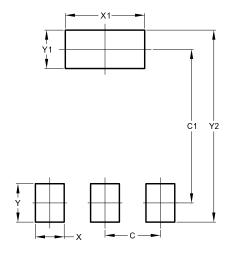
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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